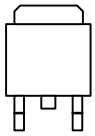
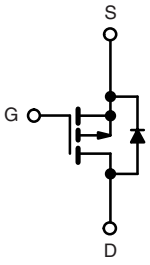
Automotive
P-Channel - 40 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY	
V_{DS} (V)	- 40
$R_{DS(on)}$ (Ω) at V_{GS} = 10 V	0.0038
$R_{DS(on)}$ (Ω) at V_{GS} = 4.5 V	0.0060
I_D (A)	120
Configuration	Single

TO-263



Top View



P-Channel MOSFET

FEATURES

- **Halogen-free According to IEC 61249-2-21 Definition**
- TrenchFET® Power MOSFET
- Package with Low Thermal Resistance
- AEC-Q101 Qualified[d]
- Compliant to RoHS Directive 2002/95/EC
- Find out more about Vishay's Automotive Grade Product Requirements at: www.vishay.com/applications

RoHS COMPLIANT
HALOGEN FREE
AUTOMOTIVE GRADE

ORDERING INFORMATION	
Package	TO-263
Lead (Pb)-free and Halogen-free	SQM110P04-04L-GE3

ABSOLUTE MAXIMUM RATINGS T_C = 25 °C, unless otherwise noted				
PARAMETER		**SYMBOL**	**LIMIT**	**UNIT**
Drain-Source Voltage		V_{DS}	- 40	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current[a]	T_C = 25 °C	I_D	- 120	A
	T_C = 125 °C		- 102	
Continuous Source Current (Diode Conduction)[a]		I_S	- 120	
Pulsed Drain Current[b]		I_{DM}	- 240	
Single Pulse Avalanche Energy	L = 0.1 mH	E_{AS}	320	mJ
Single Pulse Avalanche Current		I_{AS}	- 80	A
Maximum Power Dissipation[b]	T_C = 25 °C	P_D	375	W
	T_A = 25 °C		3.75	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to + 175	°C

THERMAL RESISTANCE RATINGS				
PARAMETER		**SYMBOL**	**LIMIT**	**UNIT**
Junction-to-Ambient	PCB Mount[c]	R_{thJA}	40	°C/W
Junction-to-Case (Drain)		R_{thJC}	0.40	

Notes

a. Package limited.
b. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
c. When mounted on 1" square PCB (FR-4 material).
d. Parametric verification ongoing.

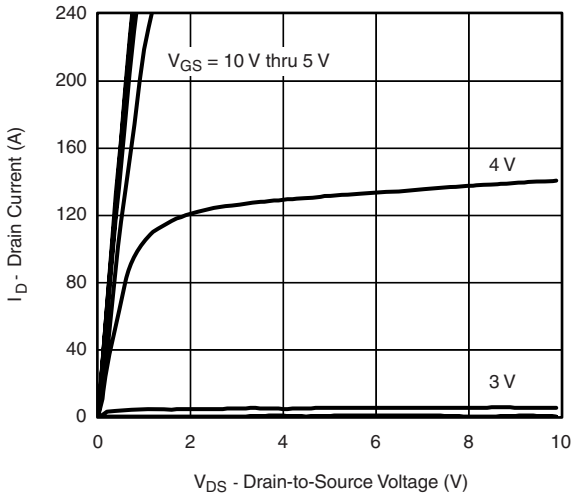
SPECIFICATIONS T_C = 25 °C, unless otherwise noted							
PARAMETER	**SYMBOL**	**TEST CONDITIONS**		**MIN.**	**TYP.**	**MAX.**	**UNIT**
Static							
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = - 250 µA		- 40	-	-	V
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = - 250 µA		- 1.5	-	- 2.5	
Gate-Source Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V		-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS} = 0 V	V_{DS} = - 40 V	-	-	- 1.0	µA
		V_{GS} = 0 V	V_{DS} = - 40 V, T_J = 125 °C	-	-	- 50	
		V_{GS} = 0 V	V_{DS} = - 40 V, T_J = 175 °C	-	-	- 250	
On-State Drain Current[a]	$I_{D(on)}$	V_{GS} = - 10 V	V_{DS} ≥ - 5 V	- 120	-	-	A
Drain-Source On-State Resistance[a]	$R_{DS(on)}$	V_{GS} = - 10 V	I_D = - 30 A	-	0.0035	0.0038	Ω
		V_{GS} = - 10 V	I_D = - 30 A, T_J = 125 °C	-	-	0.0065	
		V_{GS} = - 10 V	I_D = - 30 A, T_J = 175 °C	-	-	0.0075	
		V_{GS} = - 4.5 V	I_D = - 20 A	-	0.0050	0.0060	
Forward Transconductance[a]	g_{fs}	V_{DS} = - 15 V, I_D = - 30 A		20	-	-	S
Dynamic[b]							
Input Capacitance	C_{iss}	V_{GS} = 0 V	V_{DS} = - 25 V, f = 1 MHz	-	11 200	-	pF
Output Capacitance	C_{oss}			-	1650	-	
Reverse Transfer Capacitance	C_{rss}			-	1200	-	
Total Gate Charge[c]	Q_g	V_{GS} = - 10 V	V_{DS} = - 30 V, I_D = - 110 A	-	235	-	nC
Gate-Source Charge[c]	Q_{gs}			-	45	-	
Gate-Drain Charge[c]	Q_{gd}			-	65	-	
Turn-On Delay Time[c]	$t_{d(on)}$	V_{DD} = - 30 V, R_L = 0.35 Ω I_D ≅ - 110 A, V_{GEN} = - 10 V, R_g = 2.5 Ω		-	25	-	ns
Rise Time[c]	t_r			-	30	-	
Turn-Off Delay Time[c]	$t_{d(off)}$			-	190	-	
Fall Time[c]	t_f			-	110	-	
Source-Drain Diode Ratings and Characteristics T_C = 25 °C[b]							
Pulsed Current[a]	I_{SM}			-	-	300	A
Forward Voltage	V_{SD}	I_F = 120 A, V_{GS} = 0 V		-	1.1	1.4	V

Notes

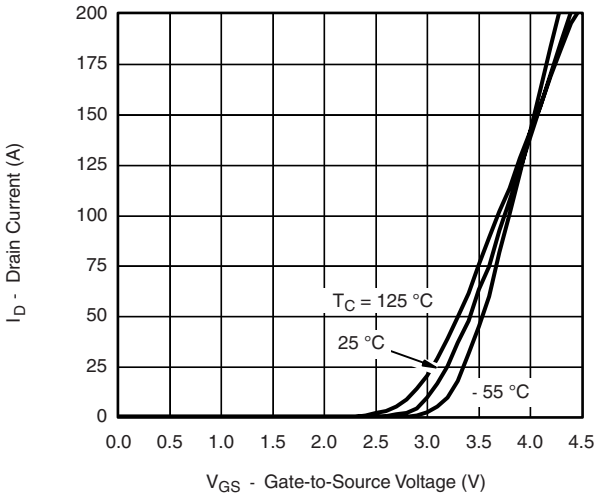
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

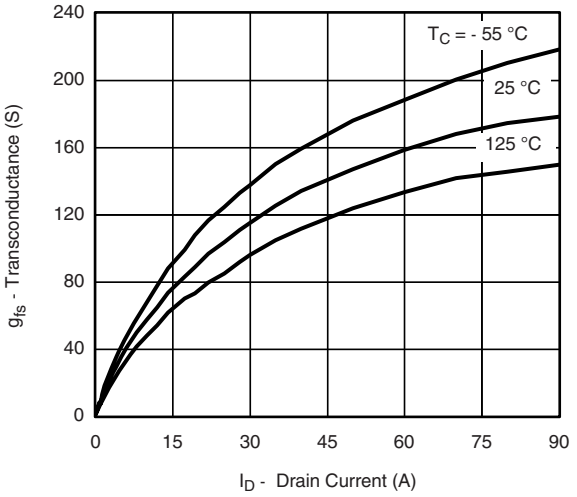
TYPICAL CHARACTERISTICS T_A = 25 °C, unless otherwise noted



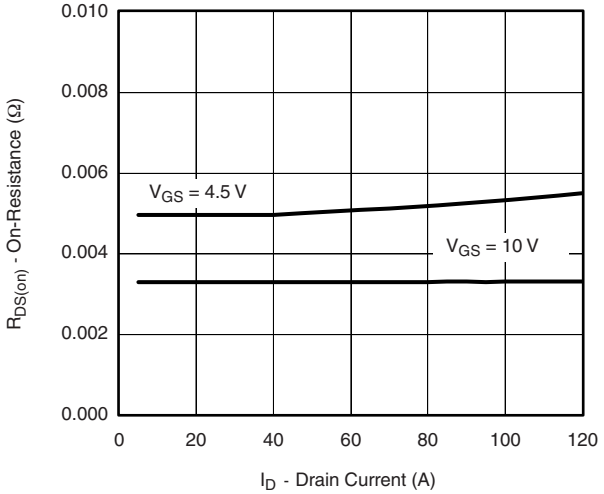
Output Characteristics



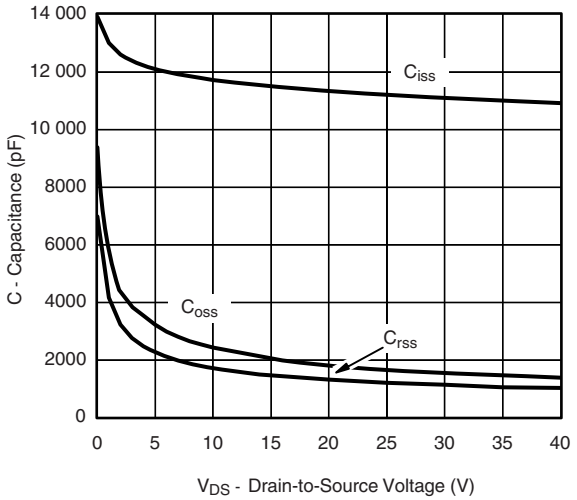
Transfer Characteristics



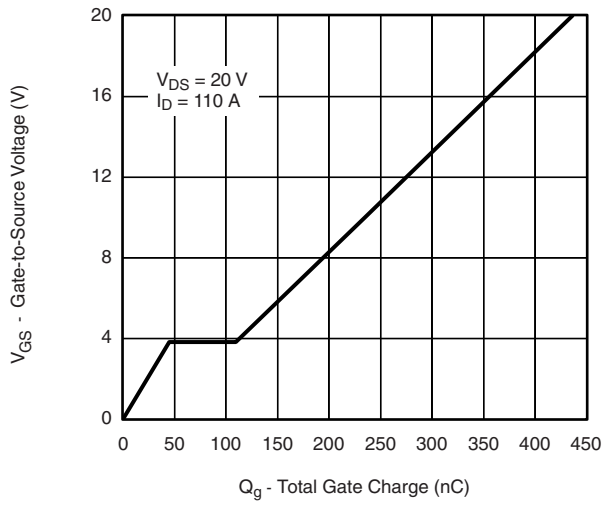
Transconductance



On-Resistance vs. Drain Current

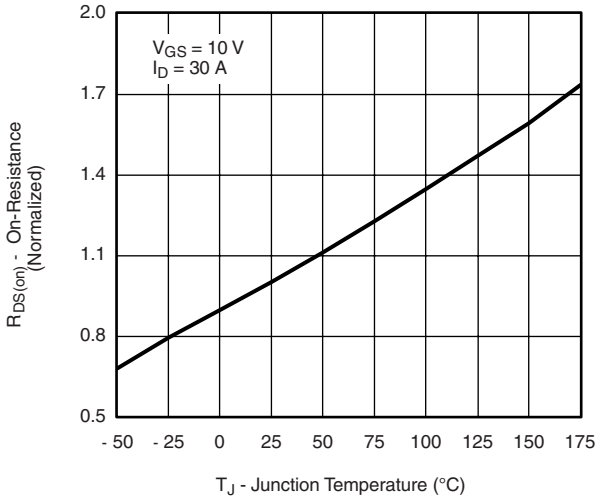


Capacitance

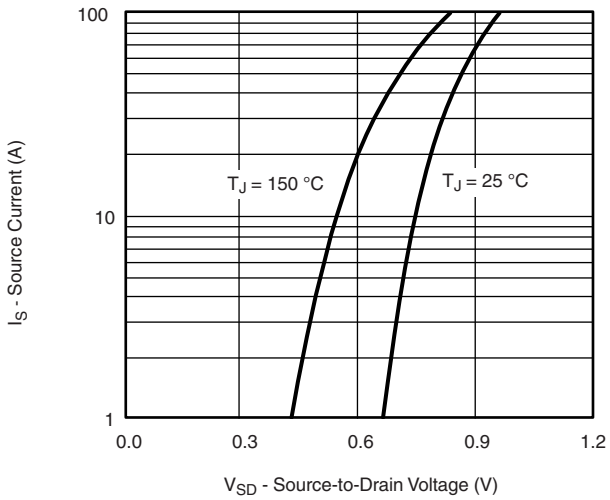


Gate Charge

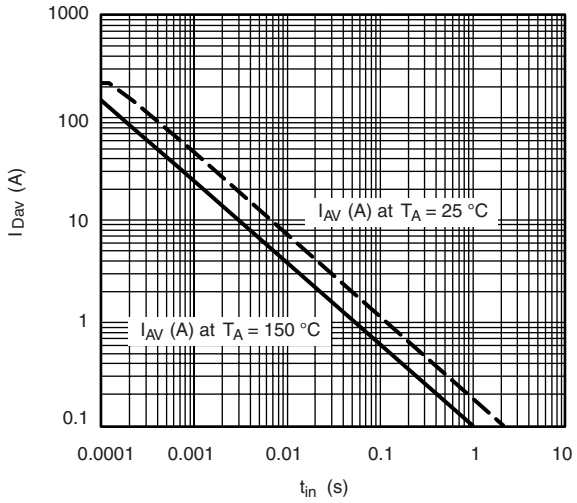
TYPICAL CHARACTERISTICS T_A = 25 °C, unless otherwise noted



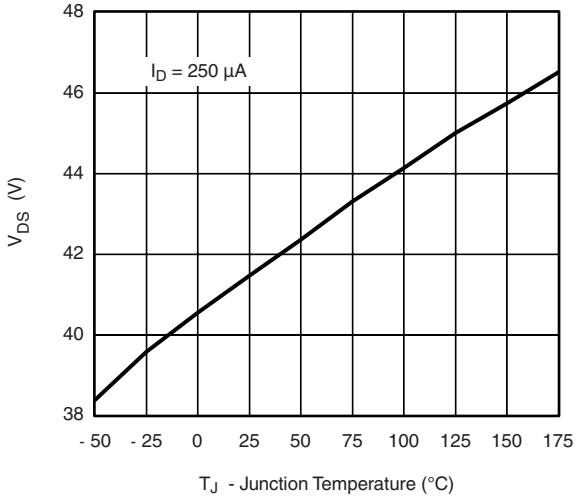
On-Resistance vs. Junction Temperature



Source Drain Diode Forward Voltage

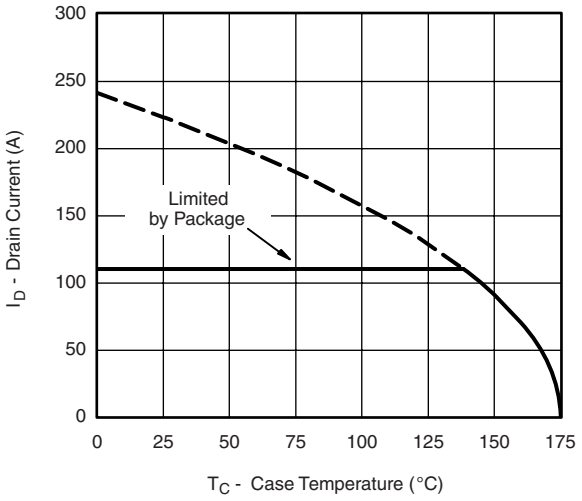


Avalanche Current vs. Time

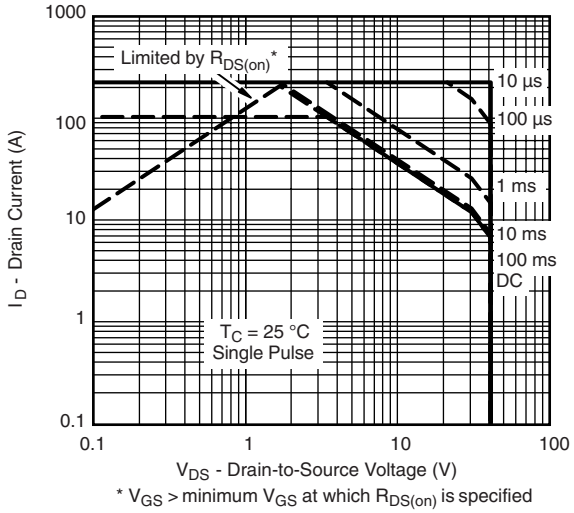


Drain Source Breakdown vs. Junction Temperature

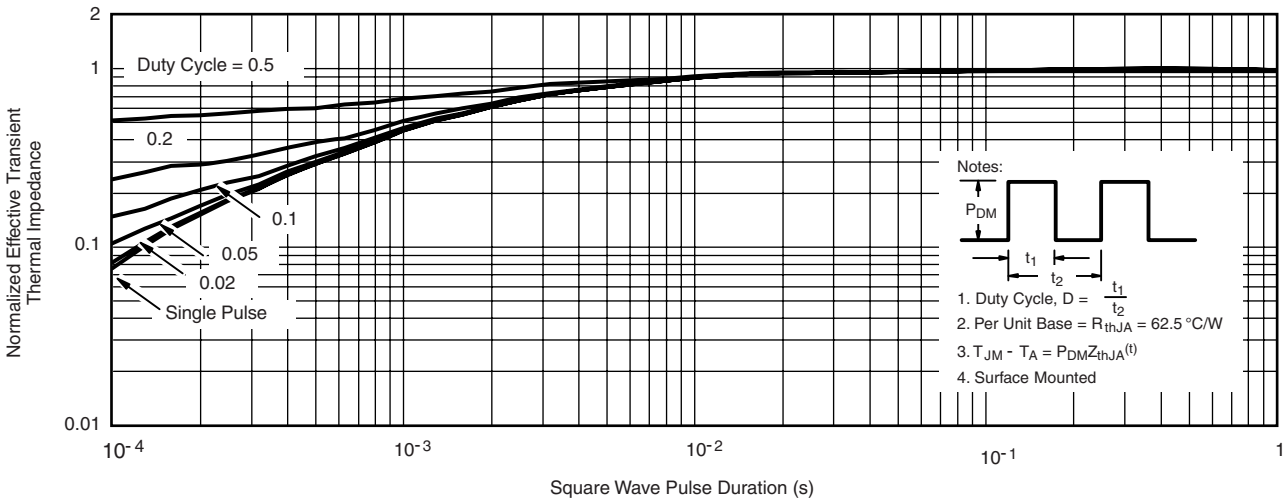
THERMAL RATINGS T_A = 25 °C, unless otherwise noted



Maximum Drain Current vs. Ambient Temperature



Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case

Note

The characteristics shown in the graph. Normalized Transient Thermal Impedance Junction to Case (25 °C) are given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

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